

MOS FIELD EFFECT TRANSISTOR 2SK2983

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

This product is N-Channel MOS Field Effect Transistor designed for high current switching application.

FEATURES

- Low on-resistance
 $R_{DS(on)1} = 20 \text{ m}\Omega$ (MAX.) ($V_{GS} = 10 \text{ V}$, $I_D = 15 \text{ A}$)
 $R_{DS(on)2} = 27 \text{ m}\Omega$ (MAX.) ($V_{GS} = 4.5 \text{ V}$, $I_D = 15 \text{ A}$)
- Low C_{iss} $C_{iss} = 1200 \text{ pF}$ TYP.
- Built-in gate protection diode

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK2983	TO-220AB
2SK2983-S	TO-262
2SK2983-ZJ	TO-263

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ^{Note1}	V_{DSS}	30	V
Gate to Source Voltage ^{Note2}	V_{GSS}	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 30	A
Drain Current (pulse) ^{Note3}	$I_{D(pulse)}$	± 120	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_T	1.5	W
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_T	50	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes1. $V_{GS} = 0 \text{ V}$

2. $V_{DS} = 0 \text{ V}$

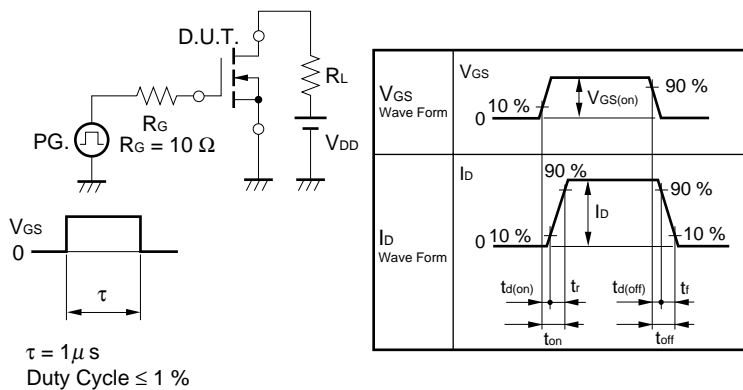
3. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1 \%$

The information in this document is subject to change without notice.

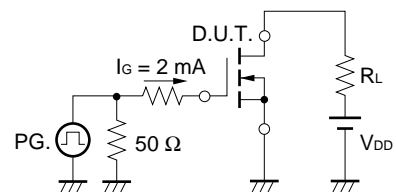
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 10 V, I _D = 15 A		13.0	20.0	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 15 A		18.0	27.0	mΩ
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.0	1.5	2.0	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 15 A	9.0	19		S
Drain Leakage Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Input Capacitance	C _{iss}	V _{DS} = 10 V		1200		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		530		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		250		pF
Turn-on Delay Time	t _{d(on)}	I _D = 15 A		50		ns
Rise Time	t _r	V _{GS(on)} = 10 V		820		ns
Turn-off Delay Time	t _{d(off)}	V _{DD} = 15 V		100		ns
Fall Time	t _f	R _G = 10 Ω		170		ns
Total Gate Charge	Q _G	I _D = 30 A		30		nC
Gate to Source Charge	Q _{GS}	V _{DD} = 24 V		4.5		nC
Gate to Drain Charge	Q _{GD}	V _{GS} = 10 V		7.5		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 30 A, V _{GS} = 0 V		0.8		V
Reverse Recovery Time	t _{rr}	I _F = 30 A, V _{GS} = 0 V		35		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A / μS		65		nC

TEST CIRCUIT 1 SWITCHING TIME

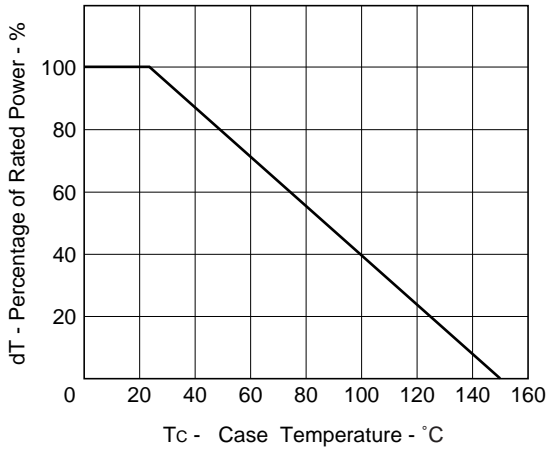


TEST CIRCUIT 2 GATE CHARGE

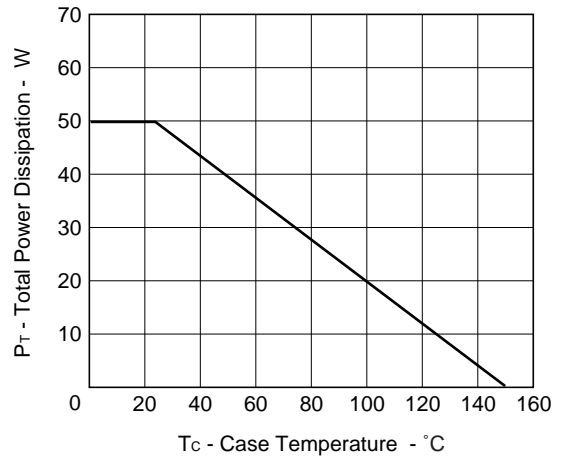


TYPICAL CHARACTERISTICS (T_A = 25 °C)

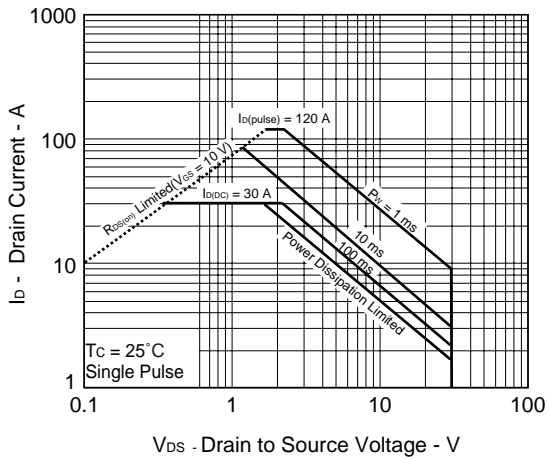
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



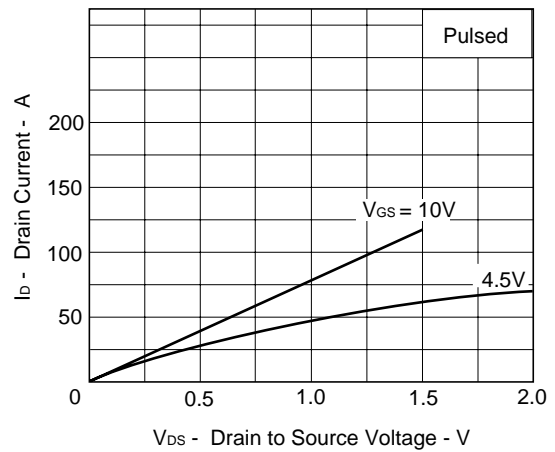
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



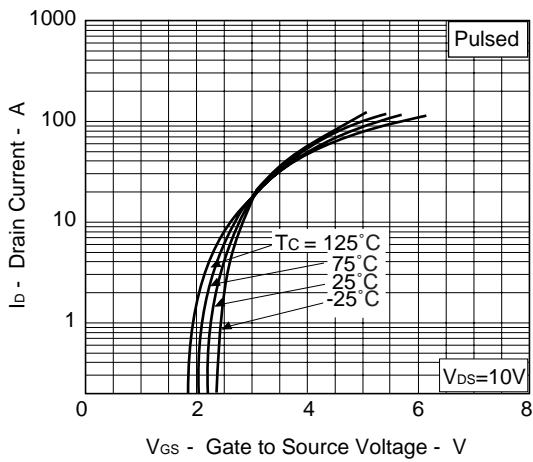
FORWARD BIAS SAFE OPERATING AREA



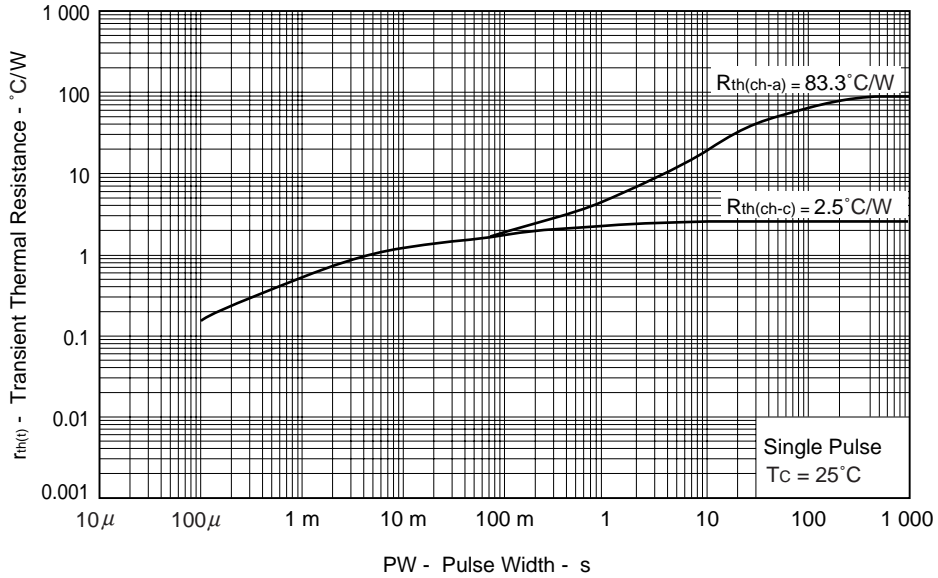
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



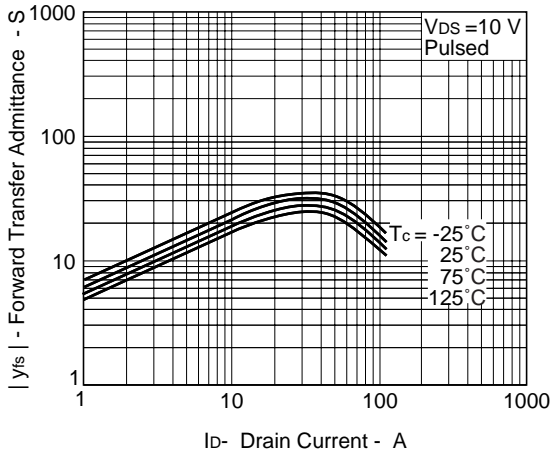
FORWARD TRANSFER CHARACTERISTICS



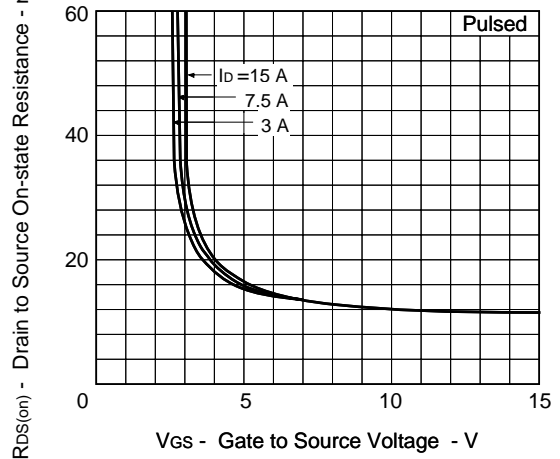
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



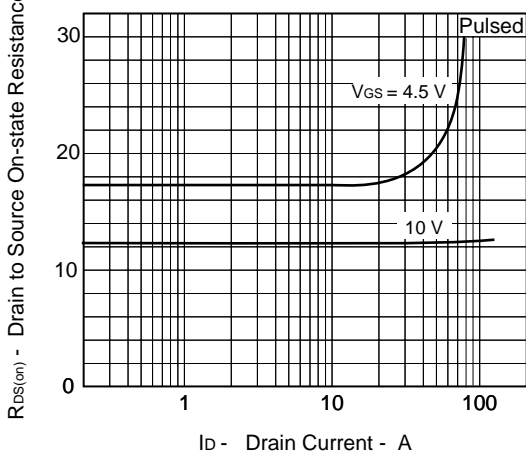
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



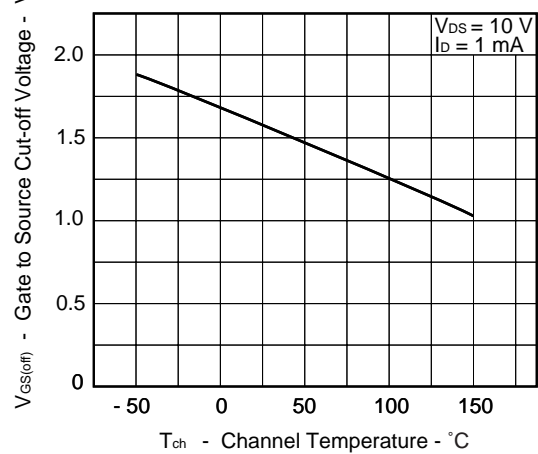
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

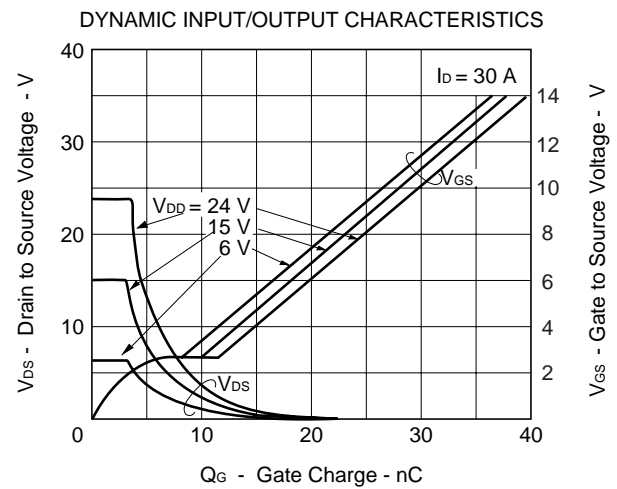
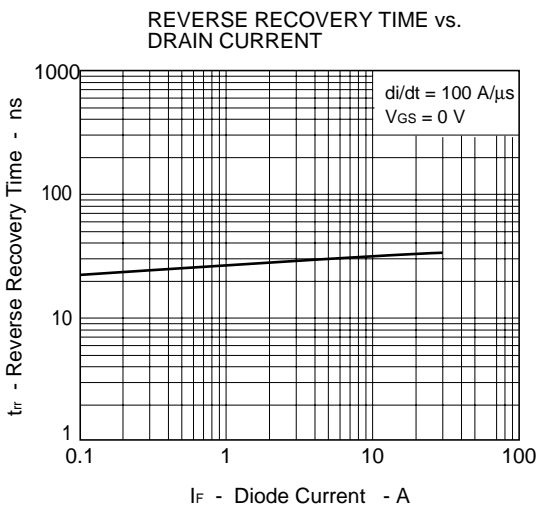
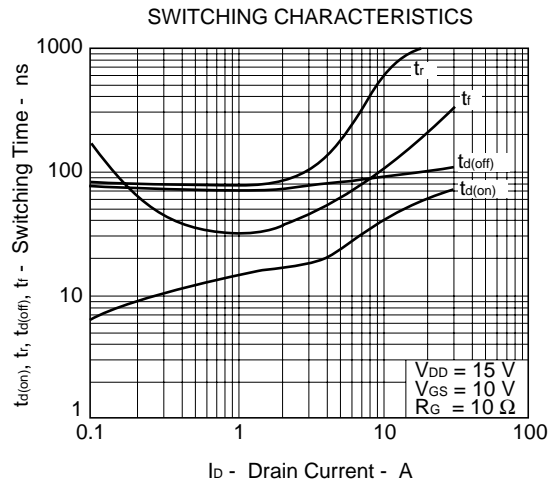
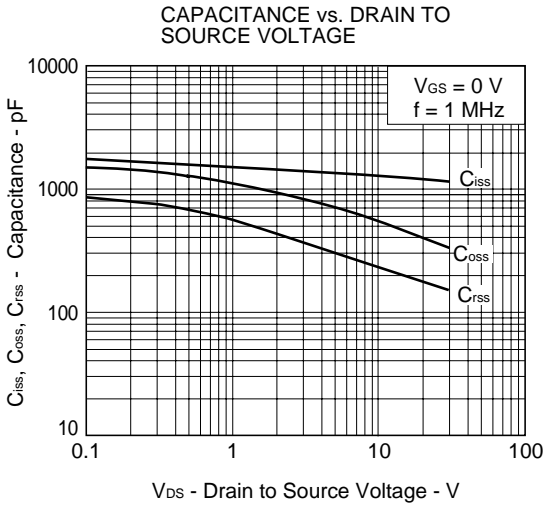
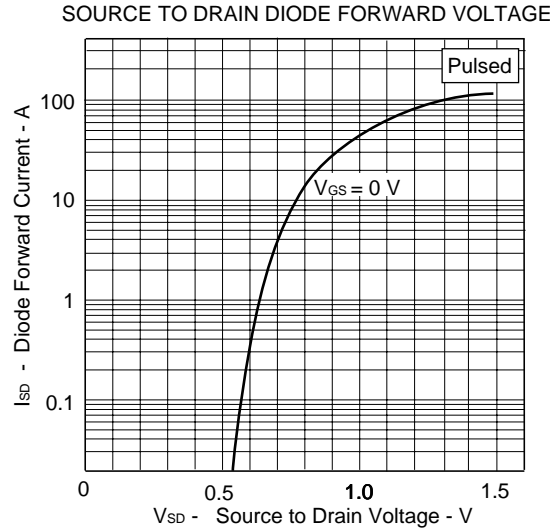
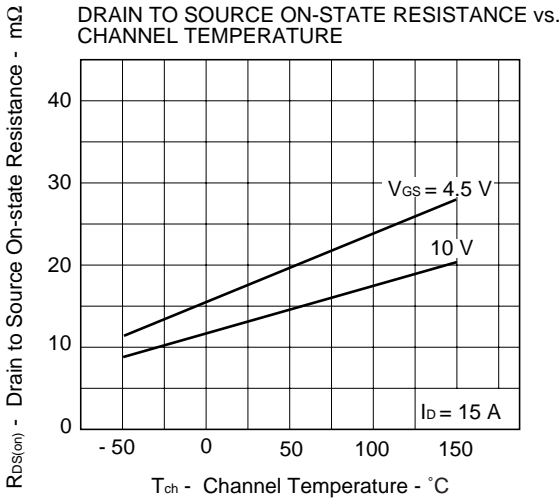


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



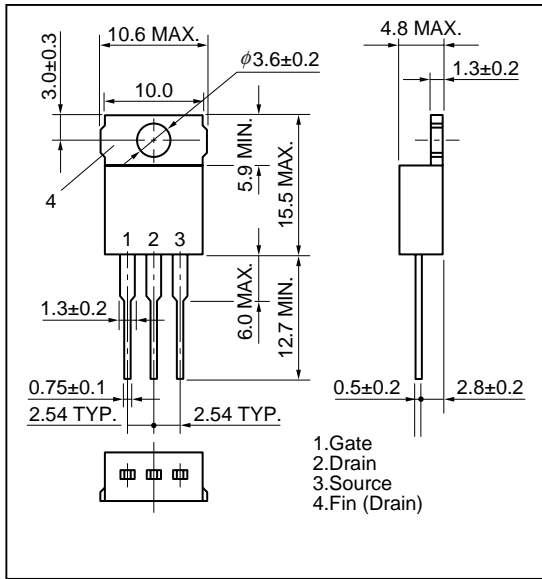
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



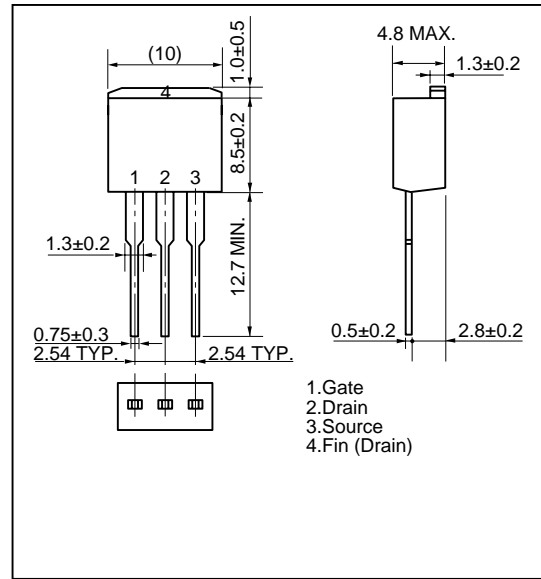


PACKAGE DRAWINGS (Unit : mm)

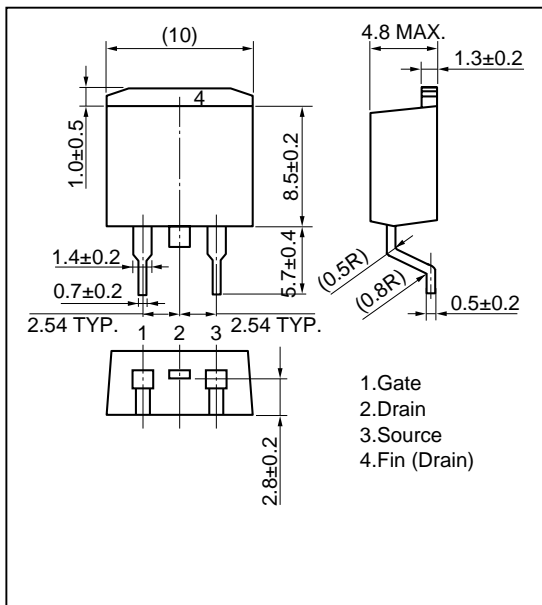
1)TO-220AB (MP-25)



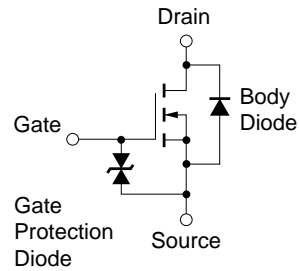
2)TO-262 (TO-220 Fin Cut:MP-25S)



3)TO-263 (JEDEC TYPE:MP-25ZJ)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device

[MEMO]

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Anti-radioactive design is not implemented in this product.